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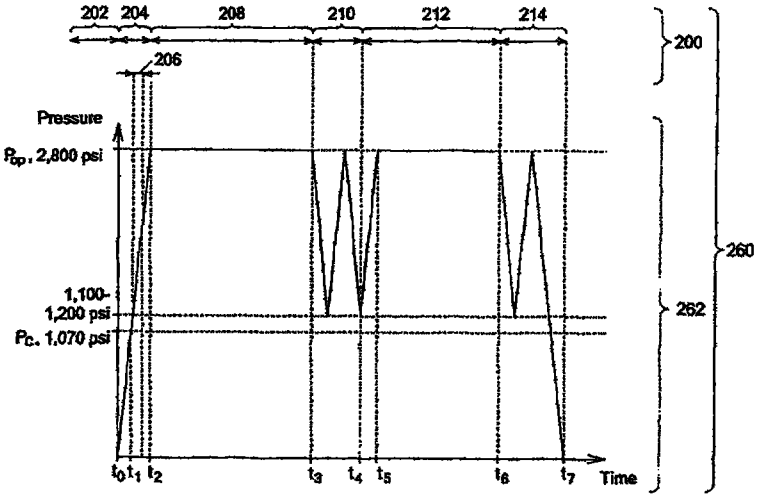
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(54) Title: REMOVAL OF PHOTORESIST AND RESIDUE FROM SUBSTRATE USING SUPERCRITICAL CARBON DIOXIDE PROCESS



(57) Abstract: A method of removing photoresist and residue from a substrate begins by maintaining supercritical carbon dioxide, an amine, and a solvent in contact with the substrate so that the amine and the solvent at least partially dissolve the photoresist and the residue. Preferably, the amine is a tertiary amine. Preferably, the solvent is selected from the group consisting of DMSO, EC, NMP, acetyl acetone, BLO, acetic acid, DMAC, PC, and a mixture thereof. Next, the photoresist and the residue are removed from the vicinity of the substrate. Preferably, the method continues with a rinsing step in which the substrate is rinsed in the supercritical carbon dioxide and a rinse agent. Preferably, the rinse agent is selected from the group consisting of water, alcohol, a mixture thereof, and acetone. In an alternative embodiment, the amine and the solvent are replaced with an aqueous fluoride.

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